

# SD103AW...SD103CW

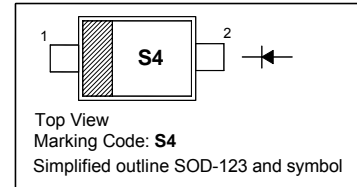
## Surface Mount Schottky Barrier Diodes

### Features

- Low Forward Voltage

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

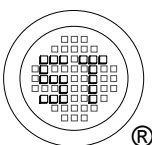


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	$V_{RRM}$	SD103AW SD103BW SD103CW	40 30 20	V
Reverse Voltage		SD103AW SD103BW SD103CW	40 30 20	V
Average Forward Rectified Current		$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	$I_{FSM}$	2	A	
Power Dissipation	$P_{tot}$	400	mW	
Operating and Storage Temperature Range	$T_j, T_{stg}$	- 65 to + 125	$^\circ\text{C}$	

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD103AW SD103BW SD103CW	40 30 20	- - -	V	
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$		$I_R$	SD103AW SD103BW SD103CW	- - -	5 5 5	$\mu\text{A}$
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$			$V_F$	- -	- -	0.37 0.6
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$			-	50	-
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$ , $I_{rr} = 0.1 I_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	10	-	ns	

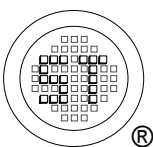
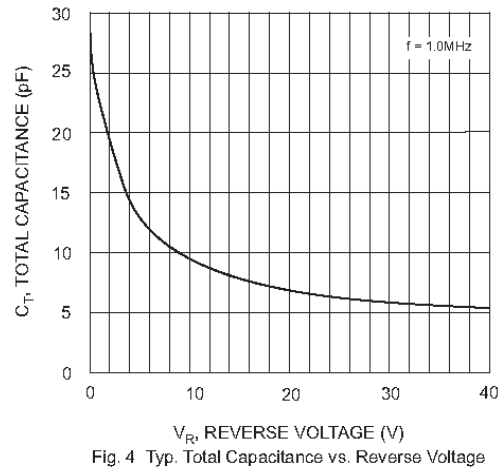
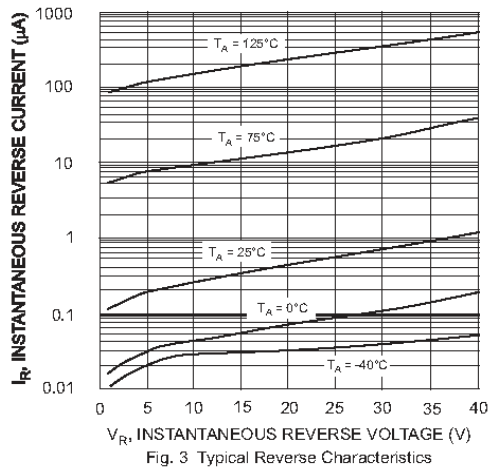
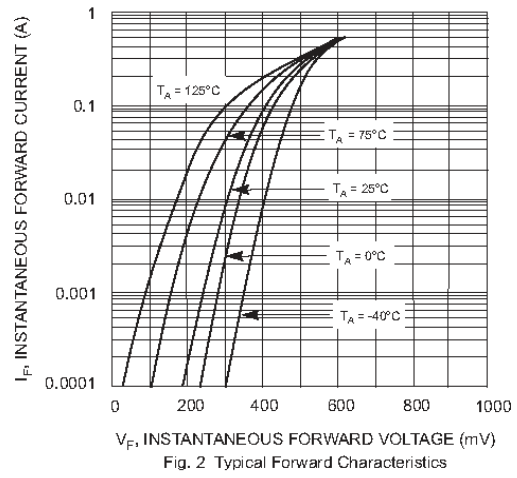
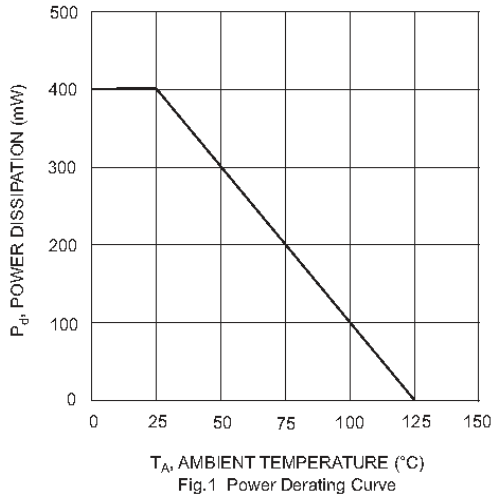


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Dated : 04/11/2009

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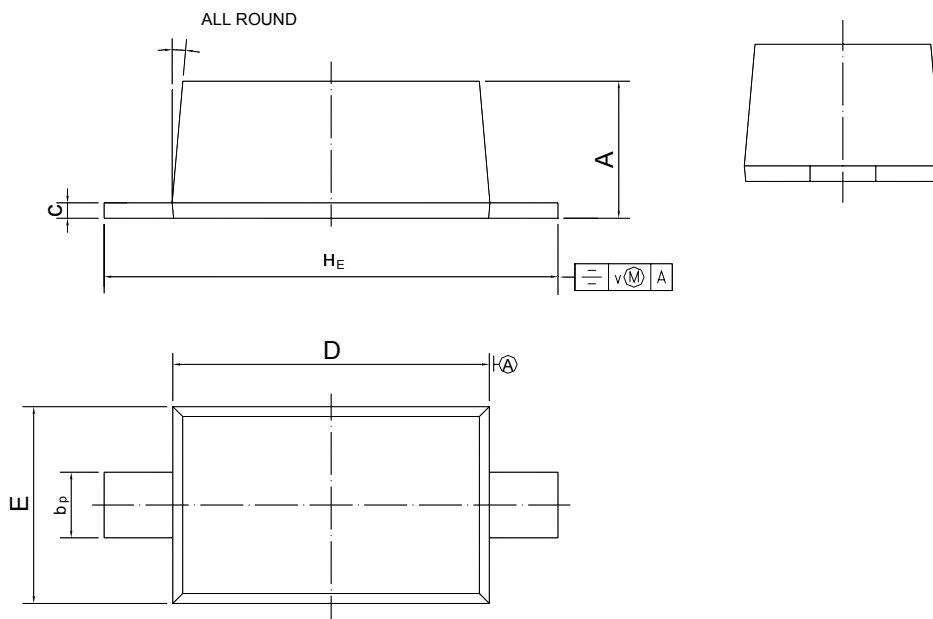
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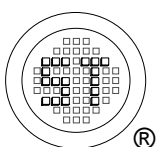
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b <sub>p</sub>	c	D	E	H <sub>E</sub>	v	
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°



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